ABSTRACT

There is provided a manufacturing process for an annealed wafer capable of reducing boron contamination occurring while annealing is performed in a state where a wafer surface after cleaning is exposed to a gas in Ar atmosphere to suppress a change in resistivity due to an increase in a boron concentration in the vicinity of the wafer surface after annealing and manufacture an annealed wafer in which a difference in a boron concentration between a surface layer portion thereof and a bulk portion thereof is essentially not a problem even if a silicon wafer having a comparative low boron concentration (1×10^{16} atoms/cm^3 or less) is used as the annealed wafer. The manufacturing process for an annealed wafer comprises: cleaning a silicon wafer; and loading the silicon wafer into a heat treatment furnace to heat-treat the silicon wafer in an Ar atmosphere, wherein an aqueous solution including hydrofluoric acid is used as a final cleaning liquid in the cleaning.